



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



ZXTDBM832

MPPS™ Miniature Package Power Solutions DUAL 20V NPN SILICON LOW SATURATION SWITCHING TRANSISTOR

SUMMARY

$V_{CE0}=20V$; $R_{SAT} = 47m\Omega$; $I_C= 4.5A$

DESCRIPTION

Packaged in the innovative 3mm x 2mm MLP (Micro Leaded Package) outline, these new 4th generation low saturation dual transistors offer extremely low on state losses making them ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users gain several other **key benefits**:

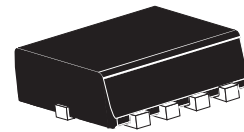
Performance capability equivalent to much larger packages

Improved circuit efficiency & power levels

PCB area and device placement savings

Lower package height (nom 0.9mm)

Reduced component count



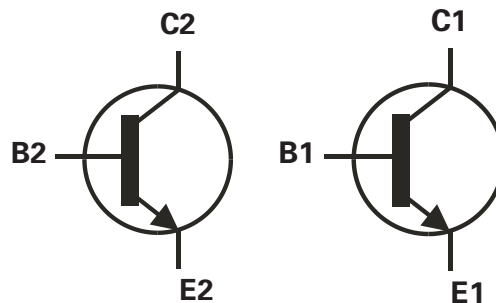
3mm x 2mm (Dual die) MLP

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (150mV @1A)
- h_{FE} characterised up to 6A
- $I_C=4.5A$ Continuous Collector Current
- 3mm x 2mm MLP

APPLICATIONS

- DC - DC Converters
- Charging circuits
- Power switches
- Motor control



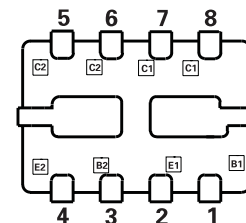
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXTDCM832TA	7''	8mm	3000
ZXTDCM832TC	13''	8mm	10000

DEVICE MARKING

DBB

PINOUT



3mm x 2mm MLP
underside view

ZXTDBM832

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	7.5	V
Peak Pulse Current	I _{CM}	12	A
Continuous Collector Current (a)(f)	I _C	4.5	A
Continuous Collector Current (b)(f)	I _C	5	A
Base Current	I _B	1000	mA
Power Dissipation at TA=25°C (a)(f)	P _D	1.5	W
Linear Derating Factor		12	mW/°C
Power Dissipation at TA=25°C (b)(f)	P _D	2.45	W
Linear Derating Factor		19.6	mW/°C
Power Dissipation at TA=25°C (c)(f)	P _D	1	W
Linear Derating Factor		8	mW/°C
Power Dissipation at TA=25°C (d)(f)	P _D	1.13	W
Linear Derating Factor		9	mW/°C
Power Dissipation at TA=25°C (d)(g)	P _D	1.7	W
Linear Derating Factor		13.6	mW/°C
Power Dissipation at TA=25°C (e)(g)	P _D	3	W
Linear Derating Factor		24	mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	R _{θJA}	83.3	°C/W
Junction to Ambient (b)(f)	R _{θJA}	51	°C/W
Junction to Ambient (c)(f)	R _{θJA}	125	°C/W
Junction to Ambient (d)(f)	R _{θJA}	111	°C/W
Junction to Ambient (d)(g)	R _{θJA}	73.5	°C/W
Junction to Ambient (e)(g)	R _{θJA}	41.7	°C/W

Notes

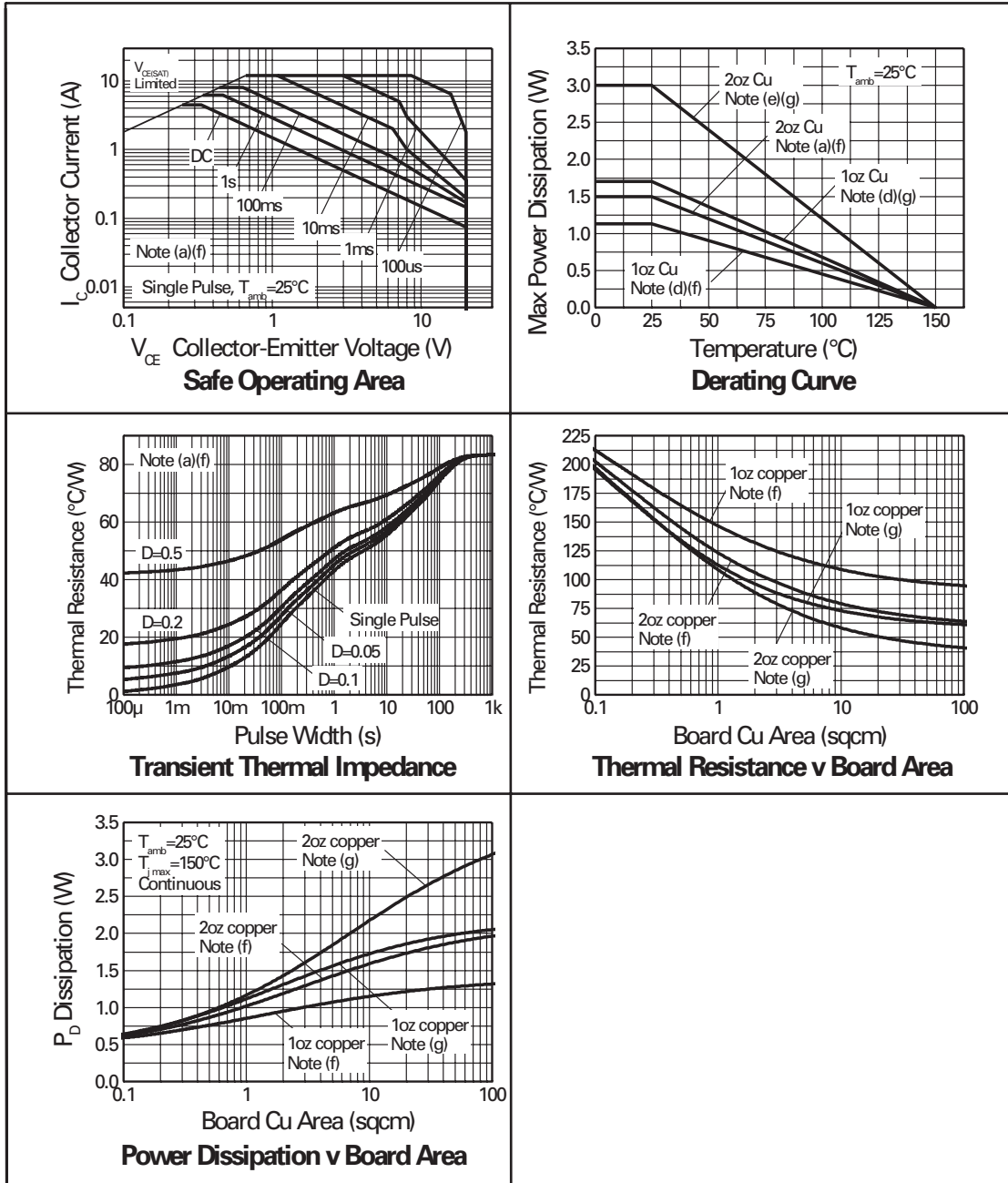
- (a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (b) Measured at t<5 secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with minimal lead connections only**.
- (d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (f) For a dual device with one active die.
- (g) For dual device with 2 active die running at equal power.
- (h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- (i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is R_{th} = 250°C/W giving a power rating of P_{tot} = 500mW.



ISSUE 1 - JUNE 2002

ZXTDBM832

TYPICAL CHARACTERISTICS



ZXTDBM832

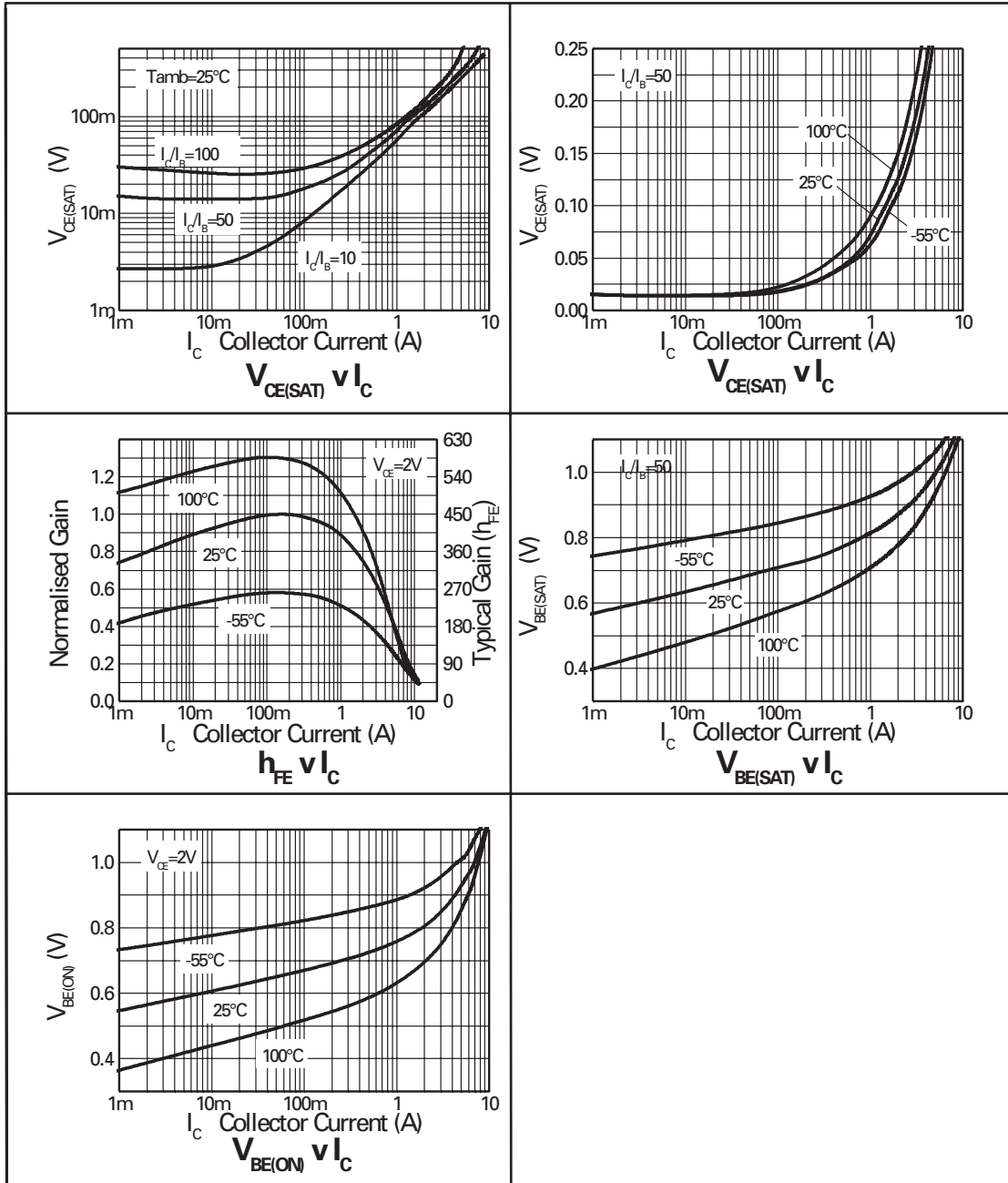
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	100		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20	27		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7.5	8.2		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			25	nA	$V_{CB}=32\text{V}$
Emitter Cut-Off Current	I_{EBO}			25	nA	$V_{EB}=6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			25	nA	$V_{CES}=16\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		8	15	mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$
			90	150	mV	$I_C=1\text{A}, I_B=10\text{mA}^*$
			115	135	mV	$I_C=2\text{A}, I_B=50\text{mA}^*$
			190	250	mV	$I_C=3\text{A}, I_B=100\text{mA}^*$
			210	270	mV	$I_C=4.5\text{A}, I_B=125\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.98	1.05	V	$I_C=4.5\text{A}, I_B=125\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.88	0.95	V	$I_C=4.5\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200	400			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$
		300	450			$I_C=0.2\text{A}, V_{CE}=2\text{V}^*$
		200	360			$I_C=2\text{A}, V_{CE}=2\text{V}^*$
		100	180			$I_C=6\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	100	140		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		23	30	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		170		ns	$V_{CC}=10\text{V}, I_C=3\text{A}$
Turn-Off Time	$t_{(off)}$		400		ns	$I_{B1}=I_{B2}=10\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle \leq 2%

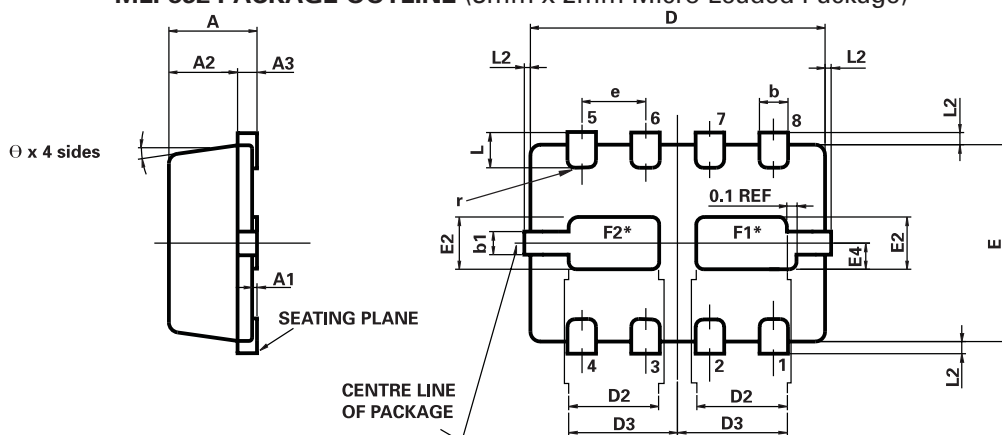
ZXTDBM832

TYPICAL CHARACTERISTICS



ZXTDBM832

MLP832 PACKAGE OUTLINE (3mm x 2mm Micro Leaded Package)



*Exposed Flags. Solder connection to improve thermal dissipation is optional.
 F1 at collector 1 potential
 F2 at collector 2 potential

CONTROLLING DIMENSIONS IN MILLIMETRES
 APPROX. CONVERTED DIMENSIONS IN INCHES

MLP832 PACKAGE DIMENSIONS

DIM	MILLIMETRES		INCHES		DIM	MILLIMETRES		INCHES	
	MIN.	MAX.	MIN.	MAX.		MIN.	MAX.	MIN.	MAX.
A	0.80	1.00	0.031	0.039	e	0.65 REF		0.0256 BSC	
A1	0.00	0.05	0.00	0.002	E	2.00 BSC		0.0787 BSC	
A2	0.65	0.75	0.0255	0.0295	E2	0.43	0.63	0.017	0.0249
A3	0.15	0.25	0.006	0.0098	E4	0.16	0.36	0.006	0.014
b	0.24	0.34	0.009	0.013	L	0.20	0.45	0.0078	0.0157
b1	0.17	0.30	0.0066	0.0118	L2	_____ 0.125		0.00	0.005
D	3.00 BSC		0.118 BSC		r	0.075 BSC		0.0029 BSC	
D2	0.82	1.02	0.032	0.040	Θ	0°	12°	0°	12°
D3	1.01	1.21	0.0397	0.0476					

© Zetex plc 2002

Europe

Zetex plc
 Fields New Road
 Chadderton
 Oldham, OL9 8NP
 United Kingdom
 Telephone (44) 161 622 4422
 Fax: (44) 161 622 4420
 uksales@zetex.com

Zetex GmbH
 Streitfeldstraße 19
 D-81673 München
 Germany
 Telefon: (49) 89 45 49 49 0
 Fax: (49) 89 45 49 49 49
 europe.sales@zetex.com

Americas

Zetex Inc
 700 Veterans Memorial Hwy
 Hauppauge, NY11788
 USA
 Telephone: (631) 360 2222
 Fax: (631) 360 8222
 usa.sales@zetex.com

Asia Pacific

Zetex (Asia) Ltd
 3701-04 Metroplaza, Tower 1
 Hing Fong Road
 Kwai Fong
 Hong Kong
 Telephone: (852) 26100 611
 Fax: (852) 24250 494
 asia.sales@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to www.zetex.com



ISSUE 1 - JUNE 2002